BYV26G

SINTERED GLASS JUNCTION
FAST AVALANCHE RECTIFIER

VOLTAGE：1400V **CURRENT: 1.05A**

GULF SEMI

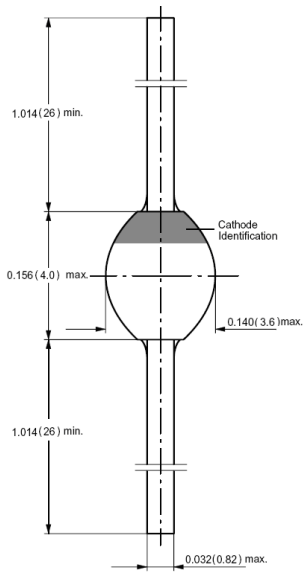
FEATURE

Glass passivated
High maximum operating temperature
Low leakage current
Excellent stability
Guaranteed avalanche energy absorption capability

MECHANICAL DATA

Case: SOD-57 sintered glass case
Terminal: Plated axial leads solderable per
MIL-STD 202E, method 208C
Polarity: color band denotes cathode end
Mounting position: any

SOD-57



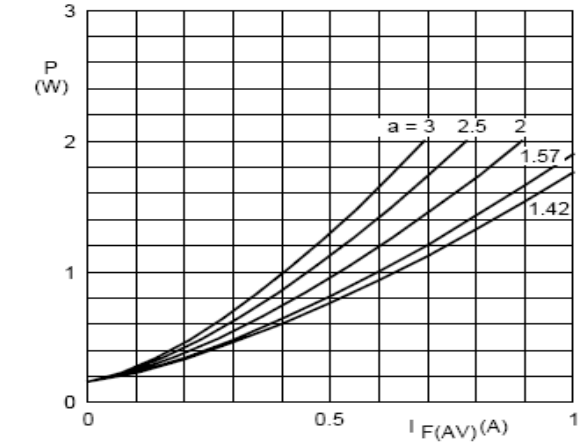
Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

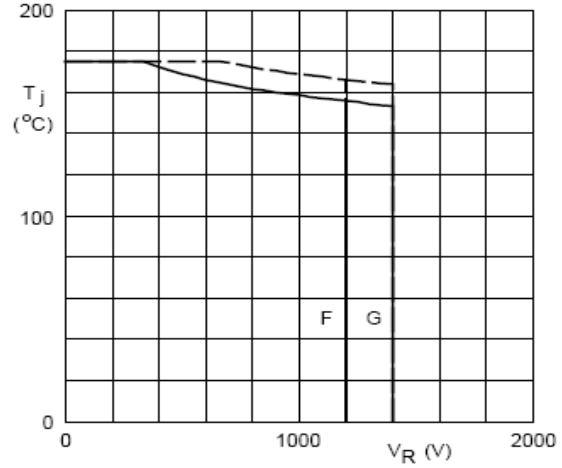
	SYMBOL	BYV26G	units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	1400	V
Maximum RMS Voltage	V_{RMS}	980	V
Maximum DC blocking Voltage	V_{DC}	1400	V
Reverse avalanche breakdown voltage IR = 0.1 mA	$V_{(BR)R}$	1500min	V
Maximum Average Forward Rectified Current 3/8"lead length at Ttp =85°C	I_{FAV}	1.05	A
Non-repetitive Peak Forward Current at t=10ms half sine wave	I_{FSM}	30	A
Maximum Forward Voltage at 1.0A	V_F	2.15	V
Non-repetitive peak reverse avalanche energy (Note 1)	E_{RSM}	10	mJ
Maximum DC Reverse Current Ta =25°C at rated DC blocking voltage Ta =165°C	I_R	5.0 150.0	μA μA
Maximum Reverse Recovery Time (Note 2)	Trr	150	nS
Diode Capacitance (Note 3)	C_d	35	pF
Typical Thermal Resistance (Note 4)	$R_{th(ja)}$	100	K/W
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175	°C

Note:
1. I_R=400mA; Tj=Tjmax prior to surge; inductive load switched off
2. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A
3. Measured at 1.0 MHz and applied reverse voltage of 0Vdc
4. Device mounted on an epoxy-glass printed-circuit board, 1.5mm thick



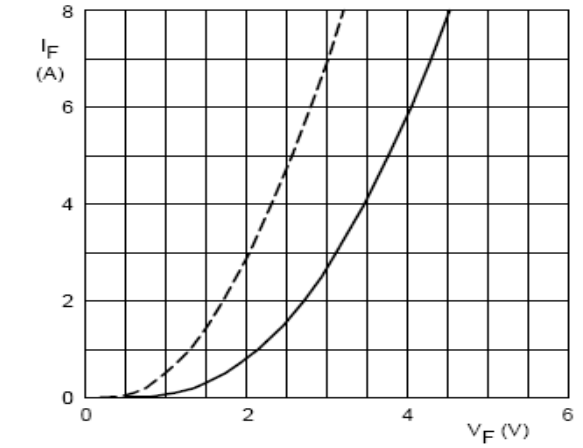
a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; δ = 0.5.

Fig.1 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



Solid line = V_R.
Dotted line = V_{RRM}; δ = 0.5.

Fig. 2 Maximum permissible junction temperature as a function of reverse voltage.



Dotted line: T_j = 175 °C.
Solid line: T_j = 25 °C.

Fig. 3 Forward current as a function of forward voltage; maximum values.

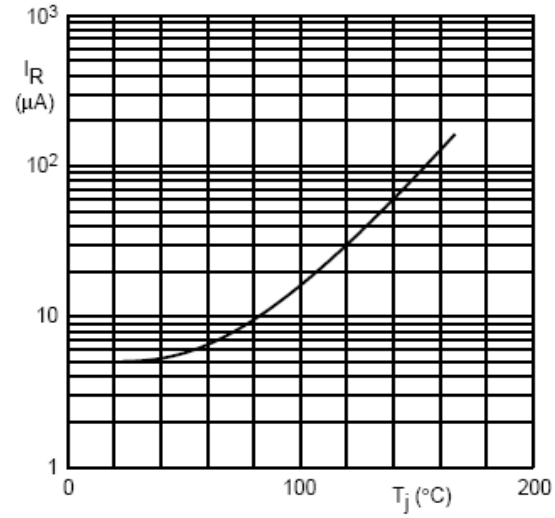
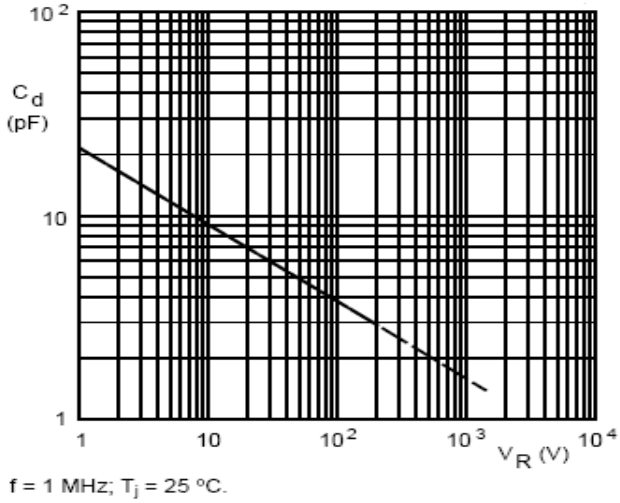


Fig.4 Reverse current as a function of junction temperature; maximum values.



f = 1 MHz; T_j = 25 °C.

Fig. 5 Diode capacitance as a function of reverse voltage, typical values.